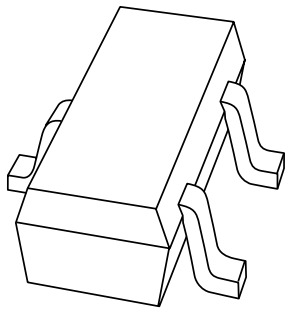


DATA SHEET



PRF949 UHF wideband transistor

Preliminary specification

1999 Oct 29

UHF wideband transistor

PRF949

FEATURES

- Small size
- Low noise
- Low distortion
- High gain
- Gold metallization ensures excellent reliability.

APPLICATIONS

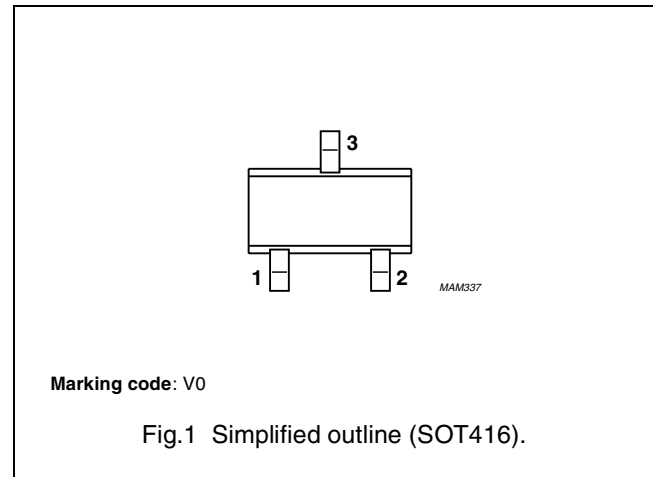
- Communication and instrumentation systems.

DESCRIPTION

Silicon NPN transistor in a surface mount 3-pin SOT416 (SC75) package. The transistor is primarily intended for wideband applications in the GHz-range in the RF front end of analog and digital cellular telephones, cordless phones, radar detectors, pagers and satellite TV-tuners.

PINNING SOT416 (SC75)

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 6$ V; $f = 1$ MHz	–	0.3	–	pF
f_T	transition frequency	$I_C = 15$ mA; $V_{CE} = 6$ V; $f_m = 1$ GHz	7	9	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 15$ mA; $V_{CE} = 6$ V; $T_{amb} = 25$ °C; $f = 1$ GHz	–	16	–	dB
NF	noise figure	$\Gamma_S = \Gamma_{opt}$; $I_C = 5$ mA; $V_{CE} = 6$ V; $f = 1$ GHz	–	1.5	2.5	dB
P_{tot}	total power dissipation	$T_s = 90$ °C; note 1	–	–	180	mW
$R_{th\ j-s}$	thermal resistance from junction to soldering point	$P_{tot} = 180$ mW	–	–	335	K/W

Note

1. T_s is the temperature at the soldering point of the collector pin.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	10	V
V_{EBO}	emitter-base voltage	open collector	–	1.5	V
I_C	DC collector current		–	50	mA
$I_{C(AV)}$	average collector current		–	50	mA
P_{tot}	total power dissipation	$T_s = 60\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	175	°C

Note

1. T_s is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	$P_{tot} = 180\text{ mW}$; $T_s = 90\text{ °C}$; note 1	335	K/W

Note

1. T_s is the temperature at the soldering point of the collector pin.

UHF wideband transistor

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CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
DC characteristics						
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 100 μA; I _E = 0	20	–	–	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 100 μA; I _B = 0	10	–	–	V
V _{(BR)EBO}	emitter-base breakdown voltage	I _E = 10 μA; I _C = 0	1.5	–	–	V
V _{BEF}	forward base-emitter voltage	I _E = 25 mA	–	–	1.05	V
I _{CBO}	collector-base leakage current	V _{CB} = 10 V; I _E = 0	–	–	100	nA
I _{EBO}	emitter-base leakage current	V _{EB} = 1 V; I _C = 0	–	–	100	nA
h _{FE}	DC current gain	I _C = 5 mA; V _{CE} = 6 V	100	150	200	
		I _C = 15 mA; V _{CE} = 6 V	–	150	–	
AC characteristics						
C _{re}	feedback capacitance	I _C = 0; V _{CB} = 6 V; f = 1 MHz	–	0.3	tbf	pF
f _T	transition frequency	I _C = 15 mA; V _{CE} = 6 V; f _m = 1 GHz	7	9	–	GHz
S ₂₁ ²	insertion gain	I _C = 15 mA; V _{CE} = 6 V; f = 1 GHz	13	15	–	dB
G _{UM}	maximum unilateral power gain; note 1	I _C = 15 mA; V _{CE} = 6 V; T _{amb} = 25 °C; f = 1 GHz	–	16	–	dB
		I _C = 15 mA; V _{CE} = 6 V; T _{amb} = 25 °C; f = 2 GHz	–	10	–	dB
NF	noise figure	Γ _S = Γ _{opt} ; I _C = 5 mA; V _{CE} = 6 V; f = 1 GHz	–	1.5	2.5	dB
		Γ _S = Γ _{opt} ; I _C = 5 mA; V _{CE} = 6 V; f = 2 GHz	–	2.1	–	dB

Note

1. G_{UM} is the maximum unilateral power gain, assuming s₁₂ is zero. $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}$ dB

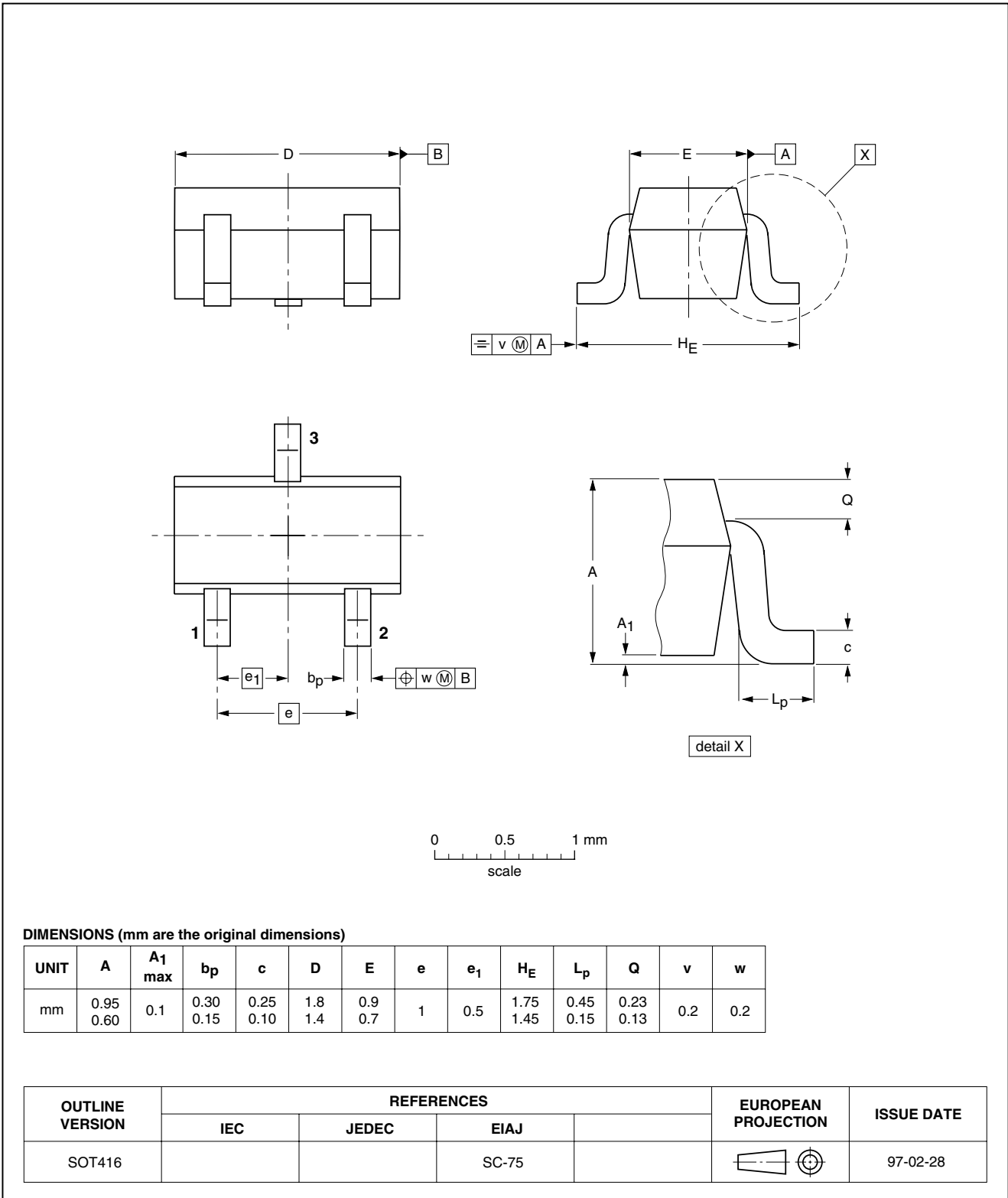
UHF wideband transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT416



UHF wideband transistor

PRF949

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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